

## Supporting Information

### Vertical oriented MoS<sub>2</sub>/Si heterojunction for ultrahigh and ultrafast photoresponse photodetector

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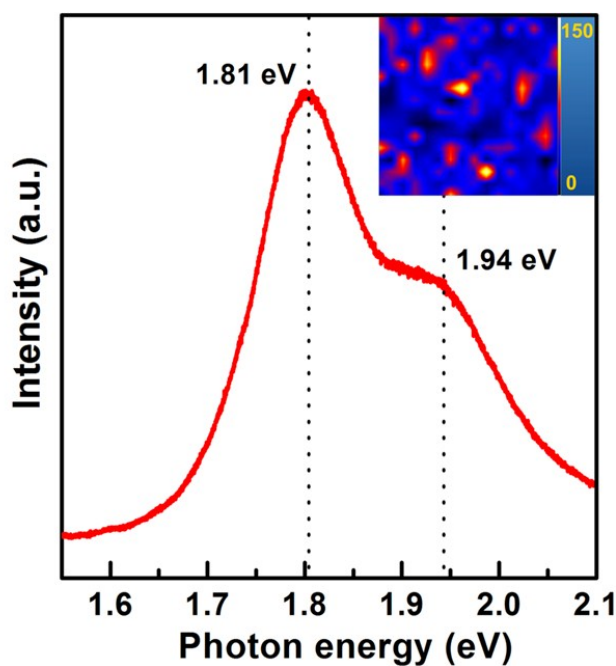


Fig. S1 PL spectra of the V-MoS<sub>2</sub> nanosheets with inset the PL mapping result.

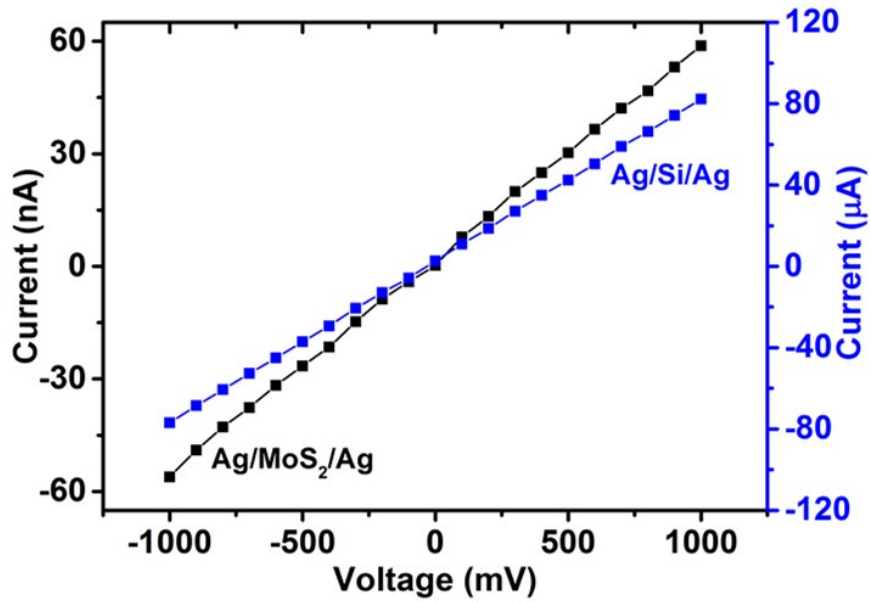


Fig. S2 The I-V curves for the Ag/MoS<sub>2</sub>/Ag structure and the Ag/Si/Ag structure, respectively.

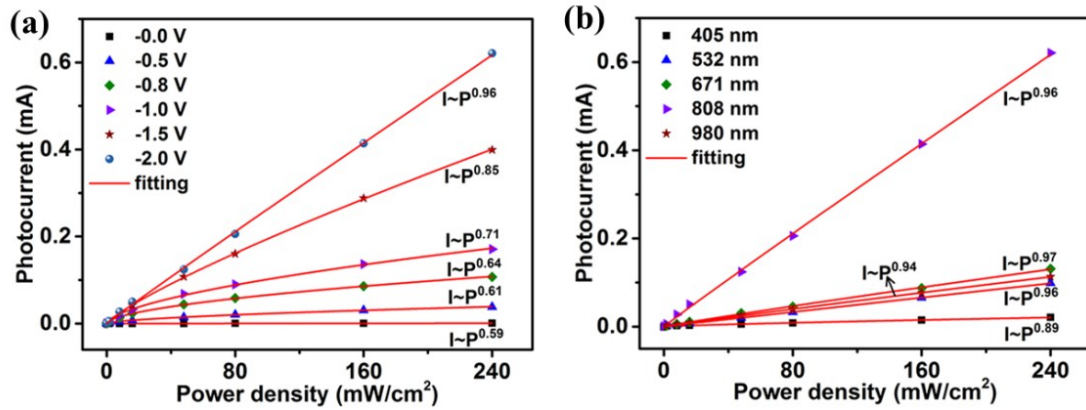
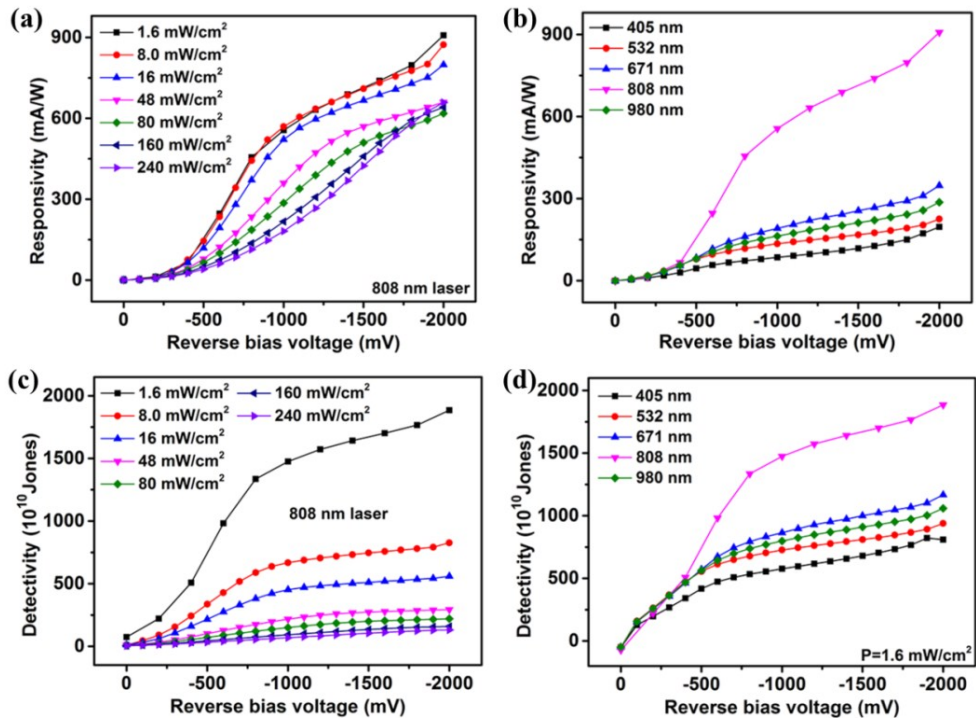
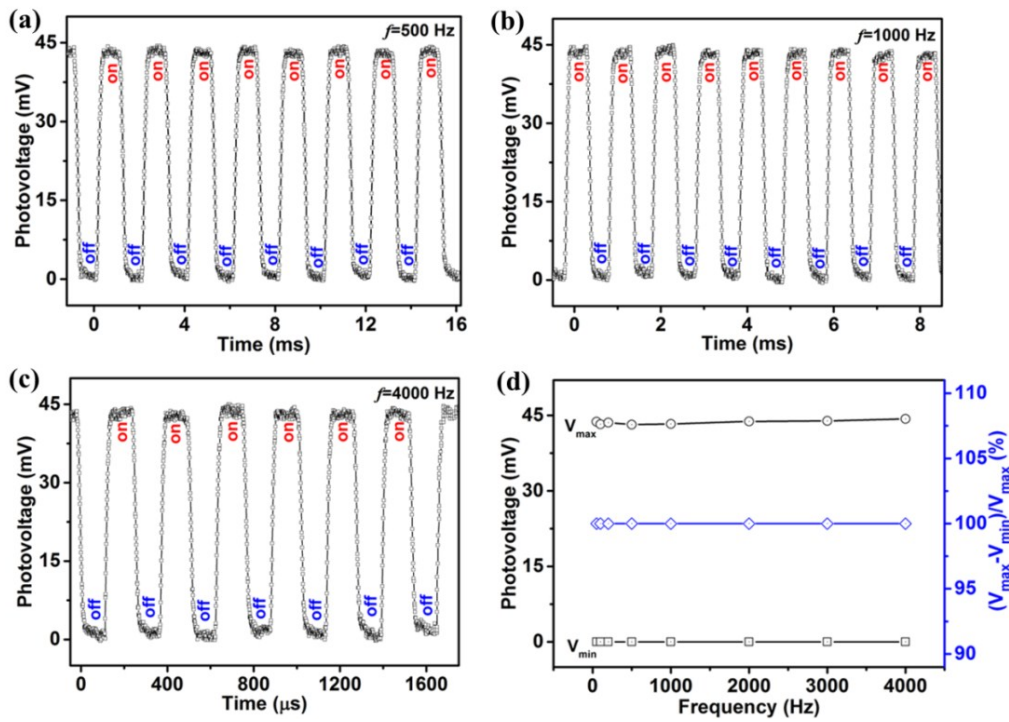


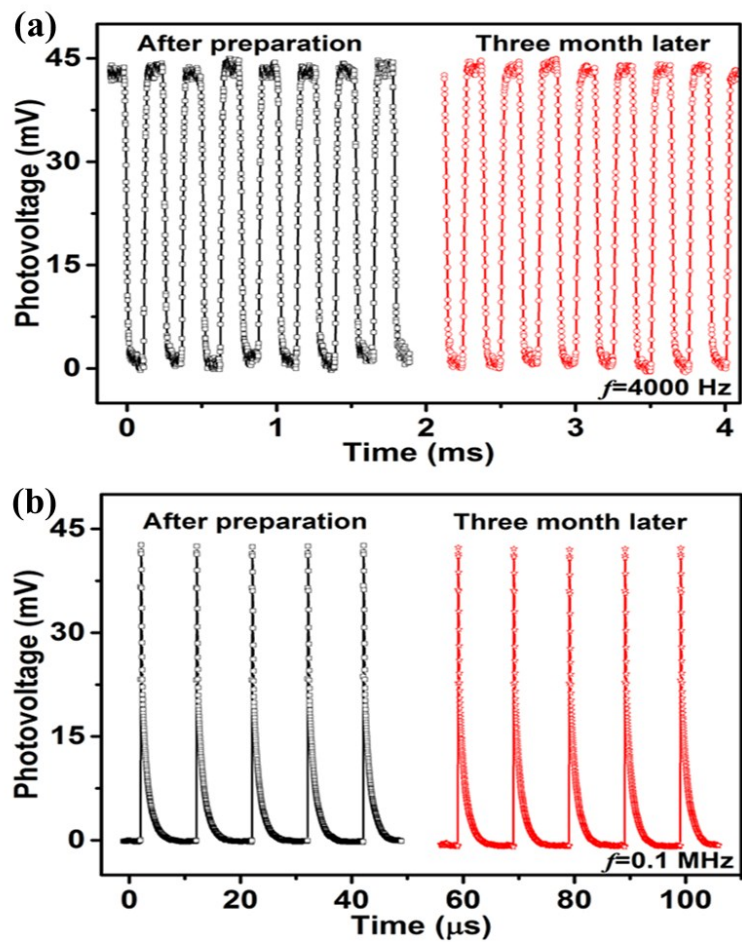
Fig. S3 (a) Photocurrent as a function of incident laser density at bias of 0 V, -0.5 V, -0.8 V, -1.0 V, -1.5 V, and -2 V. (b) Photocurrent as a function of incident laser density at bias of -2 V for different laser wavelengths.



**Fig. S4** Responsivity as a function of reverse bias voltage (a) under different illumination densities for 808 nm laser, and (b) under different wavelengths with illumination density of 1.6 mW/cm<sup>2</sup>. Detectivity as a function of reverse bias voltage (c) under different illumination densities for 808 nm laser, and (d) under different wavelengths with illumination density of 1.6 mW/cm<sup>2</sup>.



**Fig. S5** Time-dependent photovoltages at frequencies of (a) 500 Hz, (b) 1000 Hz, and (c) 4000 Hz. (d)  $V_{max}$ ,  $V_{min}$ , and relative balance  $(V_{max} - V_{min})/V_{max}$  as a function of chopper frequency.



**Fi. S6** Time-dependent photovoltages of the as-fabricated device and the same device after storage in air for three months under laser pulse frequency of (a) 4000 Hz (by chopper), and (b) 0.1 MHz (by fs-width laser).